

Title (en)  
LITHOGRAPHY DEVICE WHICH USES A SOURCE OF RADIATION IN THE EXTREME ULTRAVIOLET RANGE AND MULTI-LAYERED MIRRORS WITH A BROAD SPECTRAL BAND IN THIS RANGE

Title (de)  
LITHOGRAPHISCHES VERFAHREN MIT EUV-STRAHLENQUELLE UND BREITBAND-MEHRSCHICHTSPIEGELN

Title (fr)  
DISPOSITIF DE LITHOGRAPHIE UTILISANT UNE SOURCE DE RAYONNEMENT DANS LE DOMAINE EXTREME ULTRAVIOLET ET DES MIROIRS MULTICOUCHES A LARGE BANDE SPECTRALE DANS CE DOMAINE

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Application  
**EP 00988892 A 20001207**

Priority  
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Abstract (en)  
[origin: WO0142855A2] The invention relates to a lithography device which uses a source of radiation in the extreme ultraviolet range, and to multi-layered mirrors with a broad spectral band in this range. Each mirror (24, 26, 29) comprises a stack of layers consisting of a first material and layers consisting of a second material alternating with said first layers. The atomic number of the first material is greater than of the second material. The thickness of pairs of adjacent layers is a monotonic function of their depth in the stack. The source (22) comprises at least one target (28) which emits the radiation by interacting with a laser beam that is focused on one of its surfaces. The device uses part (36) of the radiation emitted from the other surface. The invention can be used for producing integrated circuits with a high degree of integration.

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IPC 8 full level  
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